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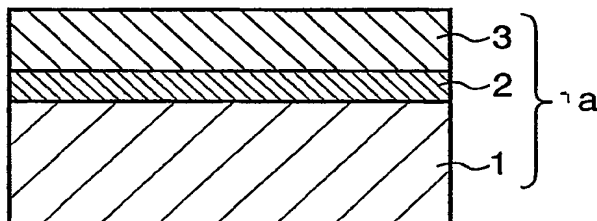
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(54) Title: SEMICONDUCTOR FILM MANUFACTURING METHOD AND SUBSTRATE MANUFACTURING METHOD



(57) Abstract: This invention provides a semiconductor film manufacturing method using a new separation technique and applications thereof. The semiconductor film manufacturing method of this invention includes a separation layer forming step of hetero-epitaxially growing a separation layer (2) on a seed substrate (1), a semiconductor film forming step of forming a semiconductor film (3) on the separation layer (2), and a separation step of separating, by using the separation layer (2), the semiconductor film (3) from a composite member (1a) formed in the semiconductor film forming step.

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